

DOCKET NO. IB-1330C

In the Specification:

Please replace the paragraph beginning at page 1, line 4 (as amended in the Preliminary Amendment dated February 12, 2001), with the following rewritten paragraph:

C1
--This application is a continuation of U.S. Patent Application Serial Number 09/259,982 filed March 1, 1999, and now issued as U.S. Patent 6,207,392 as a continuation in part of U.S. Patent Application Serial Number 08/978,450 filed November 25, 1997, and now issued as U.S. Patent 5,990,479.--

Please replace the paragraph beginning at page 11, line 24, with the following rewritten paragraph:

C2
--Formation of nanometer crystals of Group III-V semiconductors is described in copending and commonly assigned Alivisatos et al. U.S. Patent 5,751,018; Alivisatos et al. U.S. Patent 5,505,928; and Alivisatos et al. U.S. Patent 5,262,357, which also describe the formation of Group II-VI semiconductor nanocrystals, and which are also assigned to the assignee of this invention. Also described therein is the control of the size of the semiconductor nanocrystals during formation using crystal growth terminators. The teachings of Alivisatos et al. U.S. Patent 5,751,018, and Alivisatos et al. U.S. Patent 5,262,357 are each hereby specifically incorporated by reference.--
